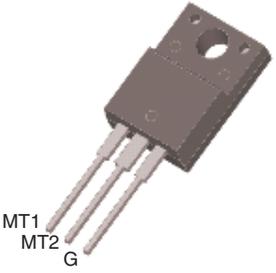
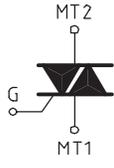


STANDARD TRIAC

<p style="text-align: center;">TO220-F (FULLY ISOLATED CASE)</p>  	<p style="text-align: center;">On-State Current Gate Trigger Current</p> <p style="text-align: center;">8 Amp $\leq 100 \text{ mA}$</p> <p style="text-align: center;">Off-State Voltage</p> <p style="text-align: center;">$200 \text{ V} \div 800 \text{ V}$</p>
	<p>This series of TRIACs uses a high performance PNPN technology.</p> <p>These parts are intended for general purpose AC switching applications with highly inductive loads.</p>

Absolute Maximum Ratings, according to IEC publication No. 134

SYMBOL	PARAMETER	CONDITIONS	Value	Unit
$I_{T(RMS)}$	RMS On-state Current (full sine wave)	All Conduction Angle, $T_C = 95^\circ\text{C}$	8	A
I_{TSM}	Non-repetitive On-State Current	Full Cycle, 60 Hz ($t = 16.7 \text{ ms}$)	88	A
I_{TSM}	Non-repetitive On-State Current	Full Cycle, 50 Hz ($t = 20 \text{ ms}$)	80	A
I^2t	Fusing Current	$t_p = 10 \text{ ms}$, Half Cycle	32	A^2s
I_{GM}	Peak Gate Current	$20 \mu\text{s max.}$ $T_j = 125^\circ\text{C}$	4	A
$P_{G(AV)}$	Average Gate Power Dissipation	$T_j = 125^\circ\text{C}$	1	W
di / dt	Critical rate of rise of on-state current	$I_G = 2x I_{GT}$, $t_r \leq 100\text{ns}$ $f = 120 \text{ Hz}$, $T_j = 125^\circ\text{C}$	50	$\text{A}/\mu\text{s}$
T_j	Operating Temperature		$(-40 + 125)$	$^\circ\text{C}$
T_{stg}	Storage Temperature		$(-40 + 150)$	$^\circ\text{C}$
T_{sld}	Soldering Temperature	10s max	260	$^\circ\text{C}$
V_{iso}	R.M.S. isolation voltage 50/60 Hz sinusoidal waveform		2.500	Vac

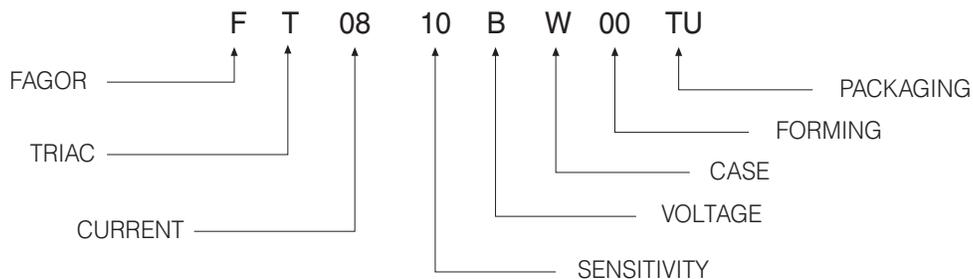
SYMBOL	PARAMETER	VOLTAGE					Unit
		B	D	M	S	N	
V_{DRM}	Repetitive Peak Off State Voltage	200	400	600	700	800	V
V_{RRM}							

STANDARD TRIAC
Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	Quadrant		SENSITIVITY				Unit
					10	13	18	17	
$I_{GT}^{(1)}$	Gate Trigger Current	$V_D = 12 V_{DC}, R_L = 33\Omega, T_j = 25^\circ C$	Q1÷Q3 Q4	MAX MAX	25 25	50 75	25 50	50 100	mA
V_{GT}	Gate Trigger Voltage	$V_D = 12 V_{DC}, R_L = 33\Omega, T_j = 25^\circ C$	Q1÷Q4	MAX	1.3				V
V_{GD}	Gate Non Trigger Voltage	$V_D = V_{DRM}, R_L = 3.3K\Omega, T_j = 125^\circ C$	Q1÷Q4	MIN	0.2				V
$I_H^{(2)}$	Holding Current	$I_T = 100 \text{ mA}, \text{ Gate open}, T_j = 25^\circ C$		MAX	25	50	25	50	mA
I_L	Latching Current	$I_G = 1.2 I_{GT}, T_j = 25^\circ C$	Q1,Q3,Q4 Q2	MAX MAX	40 60	70 80	40 80	70 100	mA
$dV/dt^{(2)}$	Critical Rate of Voltage Rise	$V_D = 0.67 \times V_{DRM}, \text{ Gate open}$ $T_j = 125^\circ C$		MIN	400	1000	700	1000	V/ μ s
$(dV/dt)_C^{(2)}$	Critical rise rate of Commu- tating off-state voltage	$(dI/dt)_C = 2.7 \text{ A/ms}$ $T_j = 125^\circ C$		MIN	3	8	5	10	V/ μ s
$V_{TM}^{(2)}$	On-state Voltage	$I_T = 11 \text{ Amp}, t_p = 380 \mu\text{s}, T_j = 25^\circ C$		MAX	1.55				V
$V_{t(o)}^{(2)}$	Threshold Voltage	$T_j = 125^\circ C$		MAX	0.85				V
$r_d^{(2)}$	Dynamic Resistance	$T_j = 125^\circ C$		MAX	60				m Ω
I_{DRM}/I_{RRM}	Off-State Leakage Current	$V_D = V_{DRM}, T_j = 125^\circ C$ $V_R = V_{RRM}, T_j = 25^\circ C$		MAX MAX	1 5				mA μ A
$R_{th(j-c)}$	Thermal Resistance Junction-Case	for AC 360° conduction angle			3.5				$^\circ C/W$
$R_{th(j-a)}$	Thermal Resistance Junction- Ambient				50				$^\circ C/W$

(1) Minimum I_{GT} is guaranteed at 5% of I_{GT} max.

(2) For either polarity of electrode MT2 voltage with reference to electrode MT1.

PART NUMBER INFORMATION


STANDARD TRIAC

Fig. 1: Maximum power dissipation versus RMS on-state current (full cycle).

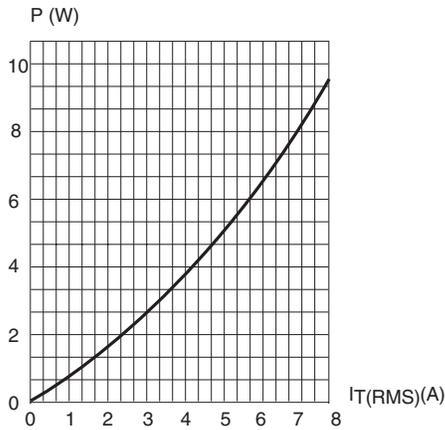


Fig. 2: RMS on-state current versus case temperature (full cycle).

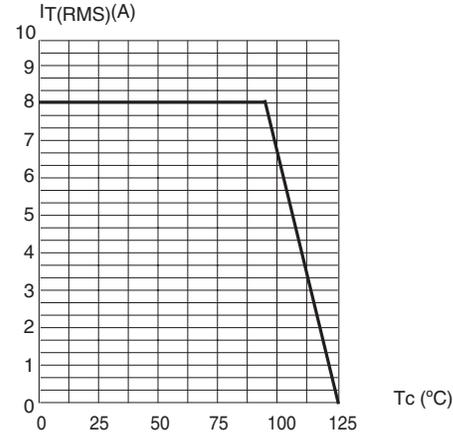


Fig. 3: Relative variation of thermal impedance versus pulse duration.

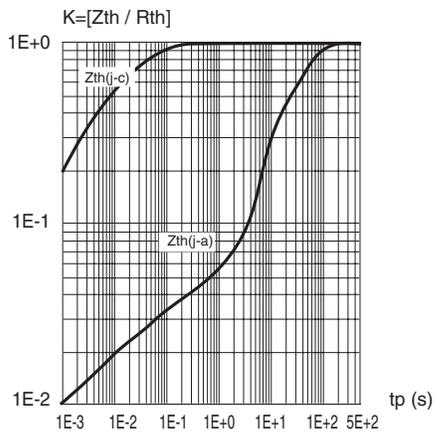


Fig. 4: On-state characteristics (maximum values)

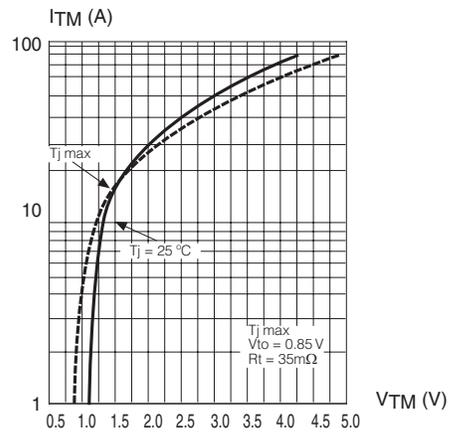


Fig. 5: Surge peak on-state current versus number of cycles

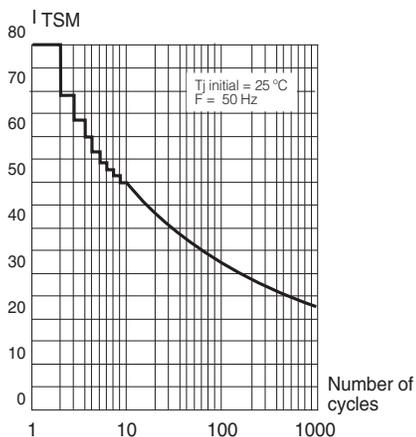
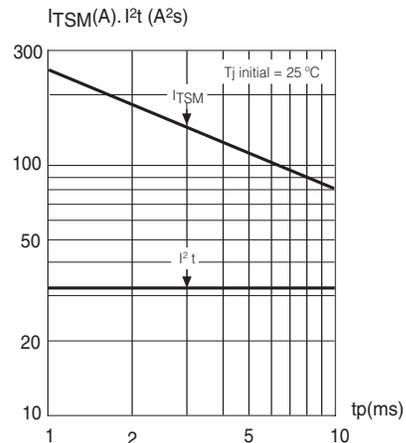


Fig. 6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$, and corresponding value of I^2t .



STANDARD TRIAC

Fig. 7: Relative variation of gate trigger current, holding current and latching versus junction temperature (typical values)

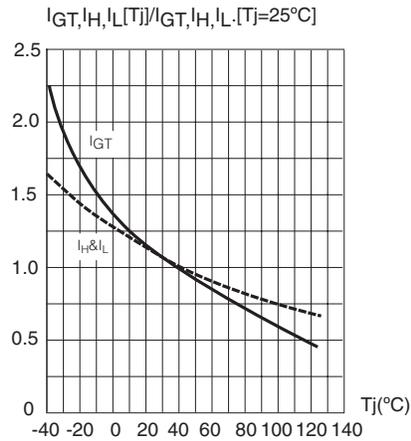


Fig. 8: Relative variation of critical rate of decrease of main current versus junction temperature

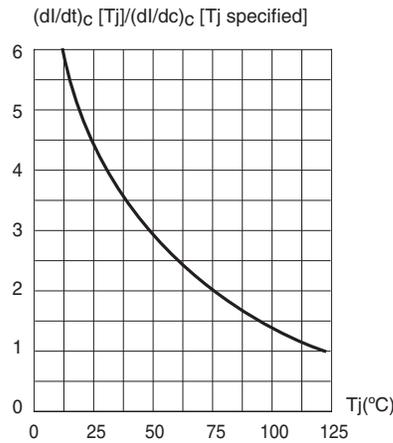
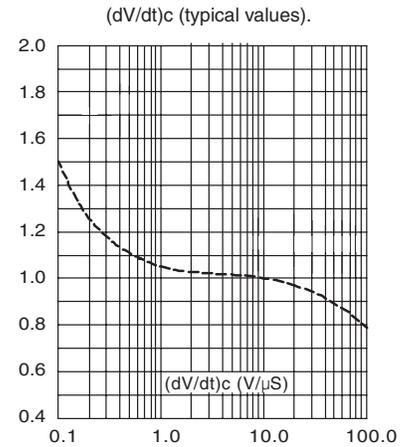


Fig. 9: Relative variation of critical rate of decrease of main current versus



PACKAGE MECHANICAL DATA TO220-F

